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Docket: 0756-958

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Continuation Application of )  
 Shunpei YAMAZAKI et al. )  
 Based on Serial No. 07/852,517 ) Art Unit: 2508  
 Filed: January 20, 1994 ) Examiner: M. Saadat  
 For: SEMICONDUCTOR MATERIAL )  
 AND METHOD FOR FORMING )  
 THE SAME AND THIN FILM )  
 TRANSISTOR ) Date: January 21, 1994

#1H/C  
 Jm  
 3/21/94

AMENDMENT

Honorable Commissioner of Patents and Trademarks  
 Washington, D.C. 20231

Sir:

Please preliminarily amend the subject application as follows:

IN THE CLAIMS:

Please cancel claims ~~1-4~~ and ~~15-22~~ and add new claims 23-28 as follows.

--23. A thin film transistor comprising:

a channel semiconductor layer comprising:

a gate insulating layer contacting said channel layer; and

a gate electrode adjacent to said channel layer with said gate

insulating layer therebetween,

C1 Sub  
 D1